



2DA1971Q

400V PNP HIGH VOLTAGE SWITCHING TRANSISTOR

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirement of Automotive Applications.

Features

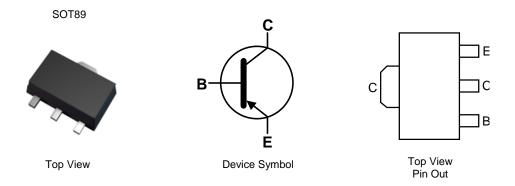
- $BV_{CEO} > -400V$
- I_C = -0.5A Continuous Collector Current
- I_{CM} = -1A Peak Pulse Current
- High Gain Holds up $h_{FE} \ge 140 @ I_C = -100 mA$
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- **PPAP Capable (Note 4)**

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.05 grams (Approximate)

Applications

High Voltage Switching



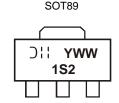
Ordering Information (Notes 4 and 5)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
2DA1971Q-7	Automotive	1S2	7	12	1,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + CI) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



1S2 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 6 = 2016)WW = Week Code (01 to 53)

1 of 7 2DA1971Q February 2018 Document number: DS39501 Rev. 2 - 2 © Diodes Incorporated



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-400	V
Collector-Emitter Voltage	$V_{\sf CEO}$	-400	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-0.5	Α
Peak Pulse Current	Ісм	-1	Α
Base Current	Ι _Β	-250	mA

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	1.5	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	83	°C/W
Thermal Resistance, Junction to Leads (Note 7)	$R_{ heta JL}$	10.4	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 25mm x 25mm 1oz copper that is on a single-sided FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

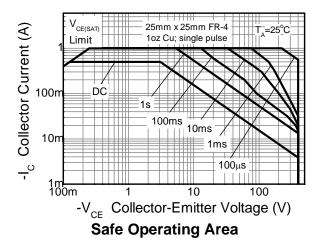
 7. Thermal resistance from junction to solder-point (on the exposed collector pad).

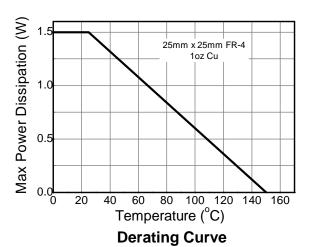
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

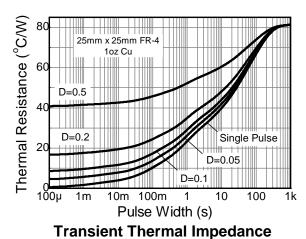
2DA1971Q 2 of 7 Document number: DS39501 Rev. 2 - 2

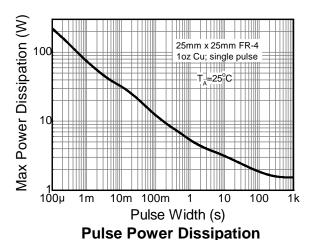


Thermal Characteristics and Derating information









February 2018 © Diodes Incorporated



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

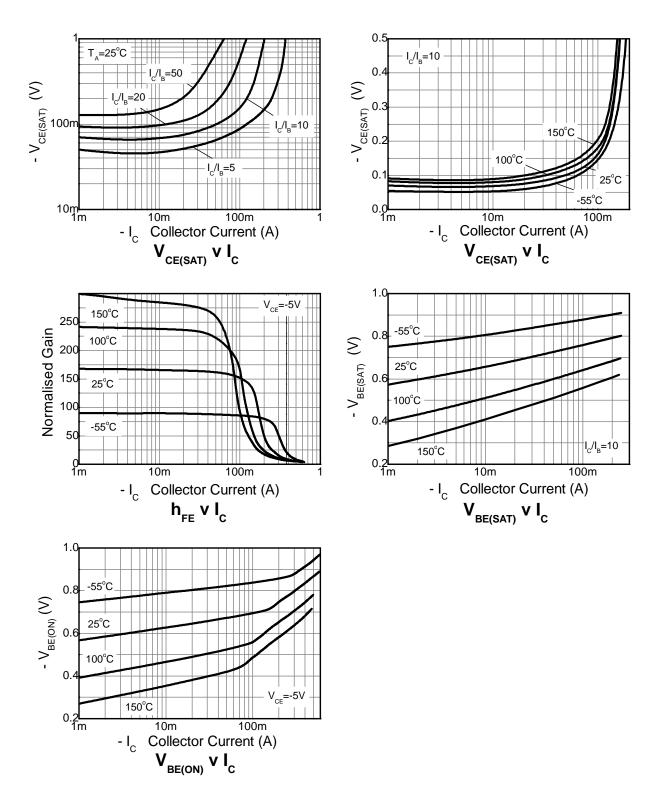
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-400	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-400	_	_	V	$I_C = -1mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	$I_E = -100 \mu A$
Collector-Emitter Cut-off Current	I _{CES}	_	_	-100	nA	V _{CE} = -320V
Collector Cut-off Current	I _{CBO}	_	_	-100	nA	V _{CB} = -320V
Emitter Cut-off Current	I _{EBO}	_	_	-100	nA	V _{EB} = -6V
Static Forward Current Transfer Ratio (Note 9)	h _{FE}	140 140	_	450 400	_	I _C = -20mA, V _{CE} = -5V I _C = -100mA, V _{CE} = -5V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(SAT)}	_	_	-250 -400	mV	I _C = -100mA, I _B = -10mA I _C = -200mA, I _B = -40mA
Base-Emitter Saturation Voltage (Note 9)	V _{BE(SAT)}	_	-0.75	-0.9	V	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(ON)}	_	_	-0.8	V	$I_C = -200 \text{mA}, V_{CE} = -10 \text{V}$
Transition Frequency	fτ	_	75	1	MHz	$I_C = -50$ mA, $V_{CE} = -5$ V, $f = 50$ MHz
Collector Output Capacitance	C _{OBO}	_	19	_	pF	$V_{CB} = -10V$, $I_{E} = 0$, $f = 1MHz$
Delay Time	t _(D)	_	89	_	ns	
Rise Time	t _(R)	_	111	_	ns	$V_{CC} = -200V, I_{C} = -100mA,$
Storage Time	t _(S)	_	2165	_	ns	$I_{B1} = -10 \text{mA}, I_{B2} = 20 \text{mA}$
Fall Time	t _(F)	_	185	_	ns	

Note:

9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

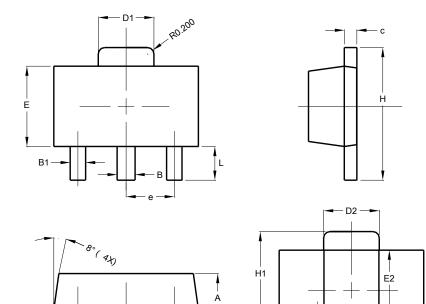




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89

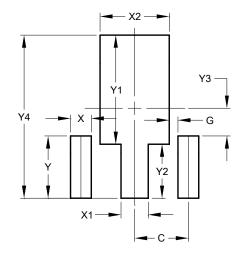


SOT89					
Dim	Min	Max	Тур		
Α	1.40	1.60	1.50		
В	0.50	0.62	0.56		
B1	0.42	0.54	0.48		
С	0.35	0.43	0.38		
D	4.40	4.60	4.50		
D1	1.62	1.83	1.733		
D2	1.61	1.81	1.71		
E	2.40	2.60	2.50		
E2	2.05	2.35	2.20		
е	-	-	1.50		
Н	3.95	4.25	4.10		
H1	2.63	2.93	2.78		
L	0.90	1.20	1.05		
L1	0.327	0.527	0.427		
Z	0.20	0.40	0.30		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value (in mm)		
С	1.500		
G	0.244		
Χ	0.580		
X1	0.760		
X2	1.933		
Y	1.730		
Y1	3.030		
Y2	1.500		
Y3	0.770		
Y4	4.530		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
 - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2018, Diodes Incorporated

www.diodes.com

7 of 7 2DA1971Q February 2018 Document number: DS39501 Rev. 2 - 2 © Diodes Incorporated

单击下面可查看定价,库存,交付和生命周期等信息

>>Diodes Incorporated(达迩科技(美台))